

SILICON POWER TRANSISTOR 2SA1847

PNP SILICON EPITAXIAL TRANSISTOR FOR HIGH-SPEED SWITCHING

The 2SA1847 is a power transistor developed for high-speed switching and features a high here at low VCE(sat). This transistor is ideal for use as a driver in DC/DC converters and actuators.

In addition, this transistor features a package that can be auto-mounted in radial taping specifications, thus contributing to mounting cost reduction.

FEATURES

- · Auto-mount possible in radial taping specifications
- · Resin-molded insulation type package with power rating of 1.8 W in stand-alone conditions
- High hee and low Vce(sat):

 $V_{CE(sat)} = -0.3 \text{ V MAX}. \ @ \text{Ic} = -6.0 \text{ V}, \ \text{Ib} = -0.3 \text{ A}$ $\text{hre} \geq 100 \ @ \text{Vce} = -2.0 \text{ V}, \ \text{Ic} = -2.0 \text{ A}$

· Fast switching speed

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Conditions	Ratings	Unit
Collector to base voltage	Vсво		-150	٧
Collector to emitter voltage	VCEO		-100	V
Emitter to base voltage	VEBO		-7.0	V
Collector current (DC)	Ic(DC)		-10	Α
Collector current (pulse)	IC(pulse)	PW \leq 300 μ s, duty cycle \leq 2%	-20	Α
Base current (DC)	I _{B(DC)}		-6.0	Α
Total power dissipation	Рт	Ta = 25°C	1.8	W
Junction temperature	Tj		150	°C
Storage temperature	T _{stg}		−55 to +150	°C

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	Vcb = -100 V, IE = 0			-10	μΑ
Collector cutoff current	ICER	$V_{CE} = -100 \text{ V}, \text{ R}_{EB} = 50 \Omega$ $Ta = 125^{\circ}\text{C}$			-1.0	mA
Collector cutoff current	ICEX1	$V_{CE} = -100 \text{ V}, V_{BE(off)} = 1.5 \text{ V}$			-10	μΑ
Collector cutoff current	ICEX2	Vce = -100 V, VbE(off) = 1.5 V Ta = 125°C			-1.0	mA
Emitter cutoff current	ІЕВО	V _{EB} = -5.0 V, I _C = 0			-10	μΑ
DC current gain	h _{FE1} *	Vce = -2.0 V, Ic = -0.5 A	100			_
DC current gain	h _{FE2} *	Vce = -2.0 V, Ic = -2.0 A	100		400	-
DC current gain	h _{FE3} *	$V_{CE} = -2.0 \text{ V}, \text{ Ic} = -6.0 \text{ A}$	60			_
Collector saturation voltage	VCE(sat)1*	Ic = -6.0 A, IB = -0.3 A			-0.3	V
Collector saturation voltage	VCE(sat)2*	Ic = -8.0 A, IB = -0.4 A			-0.5	V
Base saturation voltage	V _{BE(sat)1} *	Ic = -6.0 A, IB = -0.3 A			-1.2	V
Base saturation voltage	V _{BE(sat)2} *	Ic = -8.0 A, IB = -0.4 A			-1.5	V
Gain bandwidth product	f⊤	Vce = -10 V, Ic = -0.5 A		150		MHz
Collector capacitance	Соь	V _{CB} = -10 V, I _E = 0, f = 1 MHz		250		pF
Turn-on time	ton	Ic = -6.0 A I _{B1} = $-I_{B2}$ = -0.3 A R _L = 8.3Ω , Vcc = -50 V			0.3	μs
Storage time	tstg				1.5	μs
Fall time	tf	7 TIL — 0.3 22, VOC = -30 V			0.4	μs

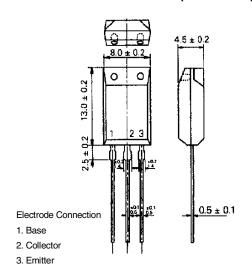
^{*} Pulse test PW \leq 350 μ s, duty cycle \leq 2%

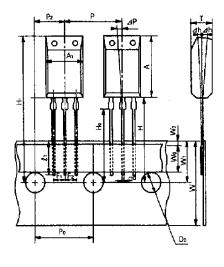
hfe CLASSIFICATION

Marking	М	L	K	
hfe	100 to 200	150 to 300	200 to 400	

PACKAGE DRAWING (UNIT: mm)

TAPING SPECIFICATION

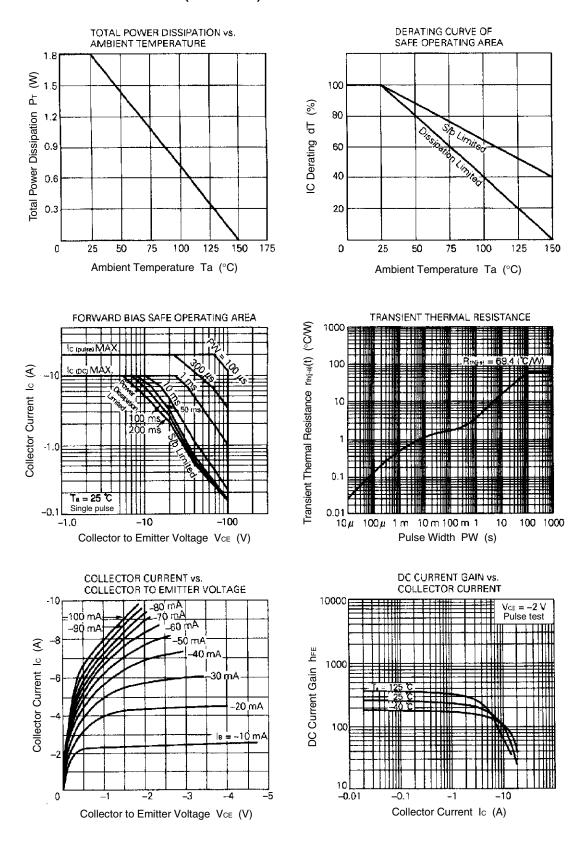




Αı	8.0 ± 0.2
Α	13.0 ± 0.2
D₀	ϕ 4.0 ± 0.2
d	0.5 ± 0.1
Fı	2.5+0.4
F ₂	2.5 -0.4
Н	20.0 MAX.
Ho	16.0 ± 0.5
Hı	32.2 MAX.
⊿fh	0 ± 1.0
٤ı	2.5 MIN.
Р	12.7 ± 1.0
P₀	12.7 ± 0.3
P₂	6.35 ± 0.5
⊿P	0 ± 1.3
T	4.5 ± 0.2
W	18.0+1.0
₩o	5.0 MIN.
Wi	9.0 ± 0.5
W ₂	0.7 MIN.
L	

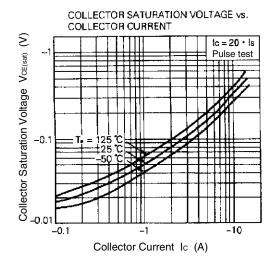


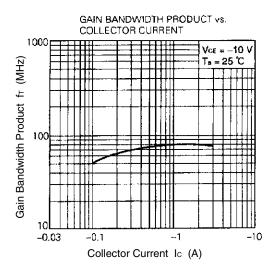
TYPICAL CHARACTERISTICS (Ta = 25°C)

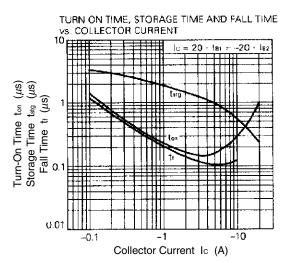


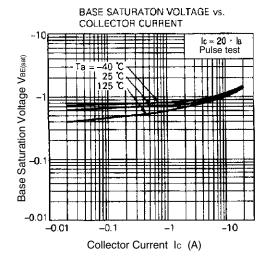
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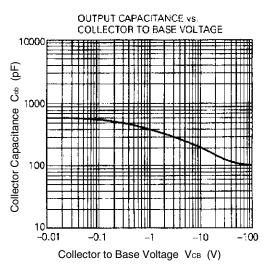
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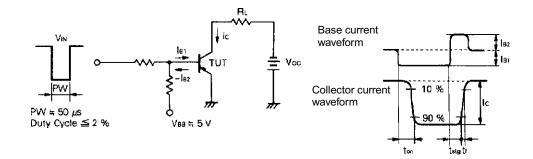








SWITCHING TIME (ton, tstg, tf) TEST CIRCUIT



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